

The rejection of claims 1 - 18 under any combination of Saran (USPN 6,232,662) and Cave (USPN 6,313,024) and Wong (USPN 2002/0132468) should be withdrawn. The instant invention is a local solution to electromigration voiding (see figures 2 - 7a and supporting text of the instant application. None of the cited art discloses, teaches or claims local solutions to electromigration voiding. Further, the Applicants' can produce a declaration under 37 CFR 1.131 removing Wong as a citation. All the claims as amended have as a limitation that the reinforcement be located on the anode end of the interconnect. Saran, Cave and Wong, alone or in any combination do not teach the theory or practice of anode end only reinforcement for any purpose.

Reconsideration and allowance of claim 1 - 18 is respectfully requested.

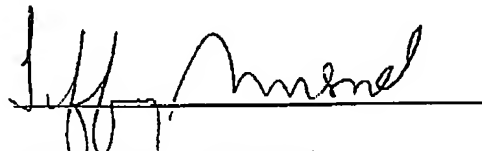
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Respectfully submitted,

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Appendix showing the Claims in Marked up Format

1. A reinforced semiconductor interconnect structure, comprising:

A first metal interconnect disposed in a first material, the first metal interconnect having a line portion and at least one via portion, an anode section and a cathode section, the via portion of the first metal interconnect located in the anode section, the line portion of the first metal interconnect having a top, bottom and terminus side, wherein at least a part of the bottom side of the line portion of the first metal interconnect in contact with the first [dielectric] material;

a first reinforcement disposed in the first material, the first reinforcement in contact with the anode section of the bottom side of the first metal interconnect, the first reinforcement comprising a second material, the second material being electrically nonconductive; and wherein the second material has a greater mechanical rigidity than the first material.